

# Dr. Saful Alam Mollick

Assistant Professor  
Department of Physics, Rabindra Mahavidyalaya  
Champadanga, Hooghly, West Bengal, India

[ResearchGate Profile](#)

## EDUCATION

---

- **Ph.D. in Physics**

Institution: University of Calcutta / Saha Institute of Nuclear Physics

Thesis Title: "*Ion-Induced Pattern Formation on Solid Surfaces*"

Timeline: Submitted August 2014; Awarded April 22, 2016

- **National Eligibility Test (NET)**

Qualified: 2006

## ACADEMIC & ADMINISTRATIVE EXPERIENCE

---

- **Assistant Professor**, Department of Physics, Rabindra Mahavidyalaya (18 December 2019 – Present)
- **Convener**, Academic and Routine Sub-committee
- **Joint Convener**, IT Sub-committee
- **Member**, PF Sub-committee
- **Member**, Career Advancement Cell Sub-committee

## TEACHING PORTFOLIO

---

Delivering core undergraduate Physics curricula across multiple specialized modules:

- **Theoretical Foundations:** Quantum Mechanics, Mathematical Physics, Thermal Physics
- **Dynamics & Waves:** Mechanics, Waves and Oscillations
- **Modern Frontiers:** Elements of Modern Physics, Astronomy and Astrophysics

## CORE RESEARCH INTERESTS

---

- **Advanced Semiconductor Etching & Surface Functionalization:** Metal-Assisted Chemical Etching (MaCE) optimization parameters (e.g., elevated temperature tracking at  $75 \pm 2^\circ\text{C}$ ); pyramidal texturing techniques for light-trapping architectures; Cold Cathode Electron Emission optimization.
- **Ion-Beam Induced Surface Instabilities & Nanopatterning:** Threshold-energy nanorippling driven by Ehrlich-Schwoebel (ES) barriers under ultra-low energy (30 eV)  $\text{Ar}^+$  ion bombardment; symmetry-driven self-organization (GaAs and Ge surfaces); substrate dynamic thermal recrystallization dynamics.
- **Mathematical & Continuum Modeling:** Solving non-linear partial differential equations integrating Kardar-Parisi-Zhang (KPZ) scaling and Herring-Mullins diffusion currents to model Atomic Force Microscopy (AFM) and Transmission Electron Microscopy (TEM) surface morphology data.

## REPRESENTATIVE PUBLICATIONS

---

1. S. Mollick, et al. "**Understanding temporal evolution of microstructures on metal-assisted chemically etched Ge surface and its applications.**" *Solar Energy*, 221, 185-196 (2021).
2. S. Mollick, et al. "**Nanorippling of ion irradiated GaAs (001) surface near the sputter-threshold energy.**" *Physica Status Solidi B*, 252(4), 811-815 (2015).
3. S. Mollick, et al. "**Homoepitaxy of germanium by hyperthermal ion irradiation.**" *Vacuum*, 107, 23-27 (2014).

## JOURNAL PUBLICATIONS

---

1. J. Mukherjee, **S. A. Mollick**, T. Basu, and T. Som.  
"Performance optimization of a microwave-coupled plasma-based ultralow-energy ECR ion source for silicon nanostructuring."  
*Beilstein Journal of Nanotechnology*, vol. 16, pp. 484–494, 2025.
2. Sudheer, R. Mandal, D. Hasina, **S. Alam Mollick**, A. Mandal, M. Ranjan, and T. Som.  
"Low-Energy Ion-Implanted Nanometer-Thick Metal Oxide Memristor for Random Number Generation at the Nanoscale."  
*ACS Applied Nano Materials*, vol. 8, no. 13, pp. 6327–6335, 2025.
3. R. Mandal, D. Hasina, A. Dutta, **S. A. Mollick**, A. Mandal, and T. Som.  
"Linearly potentiating synaptic weight modulation at nanoscale in a highly stable two-terminal memristor."  
*Applied Surface Science*, vol. 610, p. 155411, 2023.
4. **S. A. Mollick**.  
"Effect of impurities on the nanostructure formation on Ge(100) substrate by 26 keV ion implantation."  
*International Journal of Innovative Research in Technology*, vol. 10, no. 3, pp. 653–658, 2023.
5. A. Dutta, **S. A. Mollick**, P. Maiti, and T. Som.  
"Understanding temporal evolution of microstructures on metal-assisted chemically etched Ge surface and its applications."  
*Solar Energy*, vol. 221, pp. 185–196, 2021.
6. D. Hasina, M. Kumar, R. Singh, **S. A. Mollick**, A. Mitra, S. K. Srivastava, M. A. Luong, and T. Som.  
"Ion beam-mediated defect engineering in TiO<sub>x</sub> thin films for controlled resistive switching property and application."  
*ACS Applied Electronic Materials*, vol. 3, no. 9, pp. 3804–3814, 2021.
7. T. Chabri, A. Barman, S. Chatterjee, **S. A. Mollick**, and T. K. Nath.  
"Effects of transitional hysteresis on the large magnetocaloric and magnetoresistance properties of Ni-Mn-Co-Sn Heusler alloy."  
*Journal of Alloys and Compounds*, vol. 863, p. 158485, 2021.
8. **S. A. Mollick**, R. Singh, B. Satpati, S. Bhattacharyya, and T. Som.  
"Growth angle-dependent evolution of morphology and magnetic properties of Co films on highly ordered self-organized Ge substrates."  
*Journal of Magnetism and Magnetic Materials*, vol. 498, p. 166198, 2020.
9. R. Singh, **S. A. Mollick**, M. Saini, P. Guha, and T. Som.  
"Experimental and simulation studies on temporal evolution of chemically etched Si surface: Tunable light trapping and cold cathode electron emission properties."  
*Journal of Applied Physics*, vol. 125, no. 16, p. 165302, 2019.
10. **S. A. Mollick**, R. Singh, M. Kumar, S. Bhattacharyya, and T. Som.  
"Strong uniaxial magnetic anisotropy in Co films on highly ordered grating-like nanopatterned Ge surfaces."  
*Nanotechnology*, vol. 29, no. 12, p. 125302, 2018.
11. **S. A. Mollick**, M. Kumar, R. Singh, B. Satpati, D. Ghose, and T. Som.  
"Gold-decorated highly ordered self-organized grating-like nanostructures on Ge surface: Kelvin probe force microscopy and conductive atomic force microscopy studies."  
*Nanotechnology*, vol. 27, no. 43, p. 435302, 2016.
12. D. Chowdhury, D. Ghose, **S. A. Mollick**, B. Satpati, and S. R. Bhattacharyya.  
"Nanorippling of ion irradiated GaAs (001) surface near the sputter-threshold energy."  
*Physica Status Solidi B*, vol. 252, no. 4, pp. 811–815, 2015.
13. **S. A. Mollick**, D. Ghose, P. D. Shipman, and R. M. Bradley.  
"Anomalous patterns and nearly defect-free ripples produced by bombarding silicon and germanium with a beam of gold ions."  
*Applied Physics Letters*, vol. 104, no. 4, p. 043103, 2014.
14. **S. A. Mollick**, D. Ghose, S. R. Bhattacharyya, S. Bhunia, N. R. Ray, and M. Ranjan.  
"Synthesis of SiGe layered structure in single crystalline Ge substrate by low energy Si<sup>-</sup> ion implantation."  
*Vacuum*, vol. 101, pp. 387–393, 2014.

15. D. Chowdhury, D. Ghose, and **S. A. Mollick**.  
"Homoepitaxy of germanium by hyperthermal ion irradiation."  
*Vacuum*, vol. 107, pp. 23–27, 2014.
16. **S. A. Mollick**, D. Ghose, and B. Satpati.  
"Formation of Au–Ge nanodots by Au<sup>-</sup> ion sputtering of Ge."  
*Vacuum*, vol. 99, pp. 289–293, 2014.
17. **S. A. Mollick**, B. Satpati, and D. Ghose.  
"Evolution of ripples on GaAs (001) surface under low energy Ar<sup>+</sup> ion bombardment."  
*Nuclear Instruments and Methods in Physics Research Section B*, vol. 315, pp. 43–47, 2013.
18. A. Metya, D. Ghose, **S. A. Mollick**, and A. Majumdar.  
"Nanopatterning of mica surface under low energy ion beam sputtering."  
*Journal of Applied Physics*, vol. 111, no. 7, p. 074313, 2012.
19. **S. A. Mollick**, S. Karmakar, A. Metya, and D. Ghose.  
"Pit formation on the Ge (1 0 0) surfaces by normal incident Si<sup>-</sup> ion implantation."  
*Applied Surface Science*, vol. 258, no. 9, pp. 4129–4134, 2012.
20. **S. A. Mollick** and D. Ghose.  
"Formation and characterization of perpendicular mode Si ripples by glancing angle O<sub>2</sub><sup>+</sup> sputtering at room temperature."  
*Journal of Applied Physics*, vol. 106, no. 4, p. 044309, 2009.
21. P. Karmakar, **S. A. Mollick**, D. Ghose, and A. Chakrabarti.  
"Role of initial surface roughness on ion induced surface morphology."  
*Applied Physics Letters*, vol. 93, no. 10, p. 103106, 2008.

## CONFERENCE PROCEEDINGS & PREPRINTS

---

1. **S. A. Mollick**, S. R. Bhattacharyya, and D. Ghose.  
"Field emission from metal-assisted chemically etched Germanium microstructures."  
*AIP Conference Proceedings*, vol. 2265, no. 1, p. 030198, 2020.
2. **S. A. Mollick** and D. Ghose.  
"The study of the mechanical properties of Au films by nanoindentation techniques."  
*AIP Conference Proceedings*, vol. 1447, no. 1, pp. 643–644, 2012.
3. **S. A. Mollick** and D. Ghose.  
"Formation of ripple pattern on silicon surface by grazing incidence ion beam sputtering."  
*arXiv preprint arXiv:0904.1311*, 2009.

## EXPERIMENTAL VS. NUMERICAL SURFACE SCALING

---

Processing Do-main	Experimental Tools	Continuum Model Terms Applied	Selected System Metrics
<b>Chemical Etching (MaCE)</b>	AFM, FESEM, UV-vis-NIR Spectrophotometry	$\frac{\partial h}{\partial t} = -\epsilon \nabla \vec{J}_F + \sigma (\nabla h)^2 + K \nabla^4 h + \eta$	Average reflectivity < 0.23%; turn-on fields $\sim 1.7 \text{ V } \mu\text{m}^{-1}$
<b>Ion Bombardment (Ar<sup>+</sup>)</b>	AFM Tapping, XTEM (Cross-Sectional TEM)	$\sum [-\epsilon_i \partial_i (\partial_i h (1 - \delta(\partial_i h)^2))] - \sum [K_{ij} \partial_i^2 \partial_j^2 h + \sigma_{ij} \partial_i^2 (\partial_j h)^2]$	Crystalline nanowires (GaAs) and checkerboard arrays (Ge)